Complementary NPN-PNP **Power Bipolar Transistors**

These complementary devices are lower power versions of the popular NJW3281G and NJW1302G audio output transistors. With superior gain linearity and safe operating area performance, these transistors are ideal for high fidelity audio amplifier output stages and other linear applications.

Features

- Exceptional Safe Operating Area
- NPN/PNP Gain Matching within 10% from 50 mA to 3 A
- Excellent Gain Linearity
- High BVCEO
- High Frequency
- These are Pb-Free Devices

Benefits

- Reliable Performance at Higher Powers
- Symmetrical Characteristics in Complementary Configurations
- Accurate Reproduction of Input Signal
- Greater Dynamic Range
- High Amplifier Bandwith

Applications

- High-End Consumer Audio Products
 - ♦ Home Amplifiers
 - Home Receivers
- Professional Audio Amplifiers
 - Theater and Stadium Sound Systems
 - Public Address Systems (PAs)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	250	Vdc
Collector-Base Voltage	V _{CBO}	250	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector-Emitter Voltage - 1.5 V	V _{CEX}	250	Vdc
Collector Current - Continuous - Peak (Note 1)	I _C	15 30	Adc
Base Current - Continuous	Ι _Β	1.5	Adc
Total Power Dissipation @ T _C = 25°C	P_{D}	150	Watts
Operating and Storage Junction Temperature Range	T _J , T _{stg}	- 65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

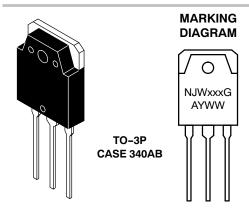
1. Pulse Test: Pulse Width = 5.0 ms, Duty Cycle < 10%.



ON Semiconductor®

http://onsemi.com

15 AMPERES **COMPLEMENTARY SILICON POWER TRANSISTORS 250 VOLTS, 150 WATTS**



= 0281 or 0302 XXXX G = Pb-Free Package = Assembly Location = Year WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
NJW0281G	TO-3P (Pb-Free)	30 Units/Rail
NJW0302G	TO-3P (Pb-Free)	30 Units/Rail

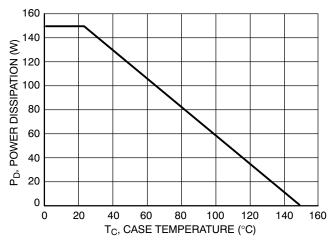
Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case		0.83	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage ($I_C = 30 \text{ mA}, I_B = 0$)	V _{CEO(sus)}	250	-	V
Collector Cutoff Current (V _{CB} = 250 V, I _E = 0)	Ісво	-	10	μΑ
Emitter Cutoff Current (V _{EB} = 5.0 V, I _C = 0)	I _{EBO}	-	5.0	μΑ
ON CHARACTERISTICS			•	•
DC Current Gain $(I_C = 0.5 \text{ A, V}_{CE} = 5.0 \text{ V})$ $(I_C = 1.0 \text{ A, V}_{CE} = 5.0 \text{ V})$ $(I_C = 3.0 \text{ A, V}_{CE} = 5.0 \text{ V})$	h _{FE}	75 75 75	150 150 150	-
Collector-Emitter Saturation Voltage (I _C = 5.0 A, I _B = 0.5 A)	V _{CE(sat)}	-	1.0	V
Base-Emitter On Voltage (I _C = 5.0 A, V _{CE} = 5.0 V)	V _{BE(on)}	-	1.2	V
DYNAMIC CHARACTERISTICS			•	•
Current-Gain - Bandwidth Product (I _C = 1.0 A, V _{CE} = 5.0 V, f _{test} = 1.0 MHz)	f⊤	30	-	MHz
Output Capacitance (V _{CB} = 10 V, I _E = 0, f _{test} = 1.0 MHz)	C _{ob}	-	400	pF



100 (E) 100 ms 100 ms

Figure 1. Power Derating

Figure 2. Safe Operating Area

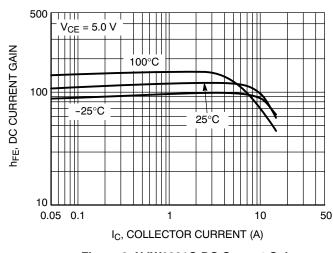


Figure 3. NJW0281G DC Current Gain

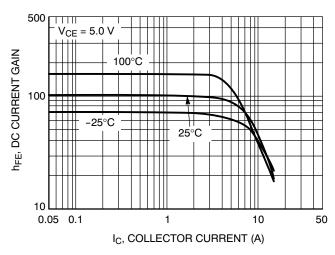


Figure 4. NJW0302G DC Current Gain

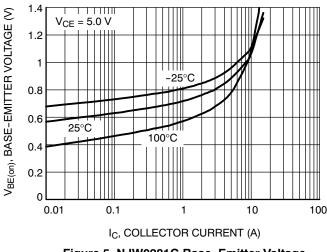


Figure 5. NJW0281G Base-Emitter Voltage

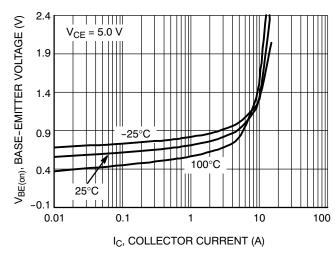


Figure 6. NJW0302G Base-Emitter Voltage

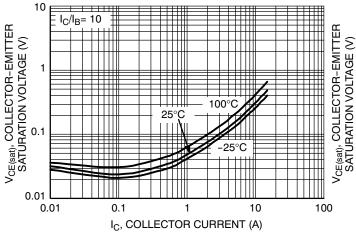


Figure 7. NJW0281G Saturation Voltage

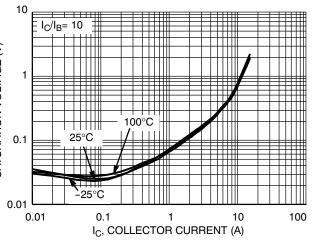


Figure 8. NJW0302G Saturation Voltage

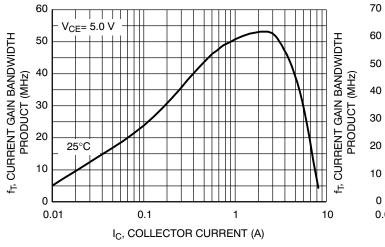


Figure 9. NJW0281G Current Gain Bandwidth Product

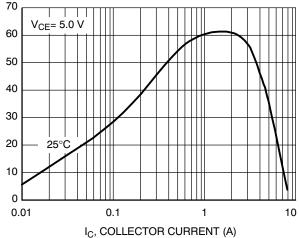
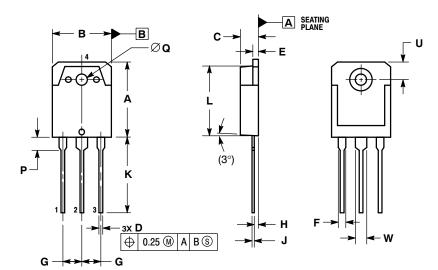


Figure 10. NJW0302G Current Gain Bandwidth Product

PACKAGE DIMENSIONS

TO-3P-3LD CASE 340AB-01 **ISSUE A**



- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM THE TERMINAL TIP.
- DIMENSION A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	19.70	19.90	20.10
В	15.40	15.60	15.80
С	4.60	4.80	5.00
D	0.80	1.00	1.20
E	1.45	1.50	1.65
F	1.80	2.00	2.20
G	5.45 BSC		
Н	1.20	1.40	1.60
J	0.55	0.60	0.75
K	19.80	20.00	20.20
L	18.50	18.70	18.90
P	3.30	3.50	3.70
Q	3.10	3.20	3.50
U	5.00 REF		
W	2.80	3.00	3.20

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice on semiconductor and are registered raderians of semiconductor Components industries, LC (SCILLC) - Scillute services in english to make changes without further induce to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor PD. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada **Fax**: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

单击下面可查看定价,库存,交付和生命周期等信息

>>ON Semiconductor(安森美)